

## Vishay Semiconductors

# **Phase Control Thyristors** (Hockey PUK Version), 1650 A



K-PUK (	A-24)
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PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	1650 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V, 1400 V, 1600 V, 1800 V, 2000 V			
$V_{TM}$	1.73 V			
I <sub>GT</sub>	100 mA			
T <sub>J</sub>	-40 °C to +125 °C			
Package	K-PUK (A-24)			
Circuit configuration	Single SCR			

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
		1650	А				
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C				
1		3080	A				
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C				
I <sub>TSM</sub>	50 Hz	30 500	^				
	60 Hz	32 000	Α				
I <sup>2</sup> t	50 Hz	4651	kA <sup>2</sup> s				
1-1	60 Hz	4250	KA-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V				
tq	Typical	200	μs				
T <sub>J</sub>		-40 to +125	°C				

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	PEAK AND OFF-STATE VOLTAGE   NON-REPETITIVE PEAK VOL		$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA					
	12	1200	1300						
	14	1400	1500						
VS-ST1200CK	16	1600	1700	100					
	18	1800	1900						
	20	2000	2100						



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ABSOLUTE MAXIMUM RATINGS		<u> </u>				T
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	L	180° condu	ction, half sine v	wave	1650 (700)	Α
at heatsink temperature	$I_{T(AV)}$	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	3080	
		t = 10 ms	No voltage		30 500	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		32 000	A kA <sup>2</sup> s
non-repetitive surge current	ITSM	t = 10 ms 100	100 % V <sub>RRM</sub>		25 700	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	26 900	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	4651	
	l <sup>2</sup> t	t = 8.3 ms			4250	
		t = 10 ms			3300	
	t = 8.3 ms reapplied			3000		
Maximum l <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms t	o 10 ms, no volt	tage reapplied	46 510	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			]
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.21	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.19	11152
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.73	V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada ayanlı 1	2 V registive lead	600	mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load		1000	] '''A	

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs			
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9				
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs	200	μs			

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA



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TRIGGERING							
DADAMETED	CVMPOL	TECT COMPLETIONS		VALUES		LIMITO	
PARAMETER	SYMBOL	15	ST CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	1	6	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	;	3	] vv	
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J \text{ maximum},$	$T_J = T_J$ maximum, $t_p \le 5$ ms		<u>.</u> 0	V	
Maximum peak negative gate voltage	- V <sub>GM</sub>				5.0		
		T <sub>J</sub> = -40 °C		200	-		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger/	100	200	mA	
		T <sub>J</sub> = 125 °C	J = 125 °C current/voltage are the lowest		-		
		T <sub>J</sub> = -40 °C	value which will trigger all units	1.4	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V	
		T <sub>J</sub> = 125 °C		0.9	-		
DC gate current not to trigger	I <sub>GD</sub>		Maximum gate current/voltage	10		mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal resistance, junction to heatsink	В	DC operation single side cooled	0.0.42			
	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance,		DC operation single side cooled	0.006	<b>1</b> √ <b>V</b> V		
ease to heatsink		DC operation double side cooled	0.003			
Mounting force, ± 10 %				N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet K-PUK (A-24)		(A-24)		

△R <sub>thJC</sub> CONDUCTION									
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	RCONDUCTION	TECT CONDITIONS	UNITS			
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS			
180°	0.003	0.003	0.002	0.002					
120°	0.004	0.004	0.004	0.004					
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W			
60°	0.007	0.007	0.007	0.007					
30°	0.012	0.012	0.012	0.012					

#### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC



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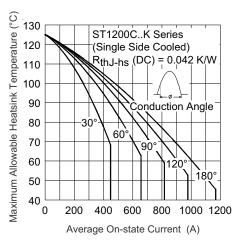


Fig. 1 - Current Ratings Characteristics

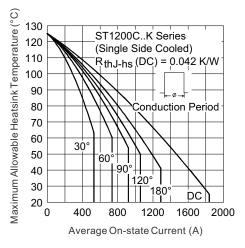


Fig. 2 - Current Ratings Characteristics

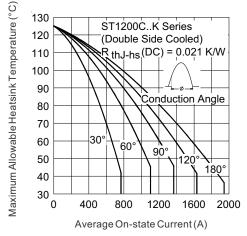


Fig. 3 - Current Ratings Characteristics

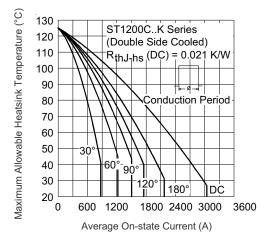


Fig. 4 - Current Ratings Characteristics

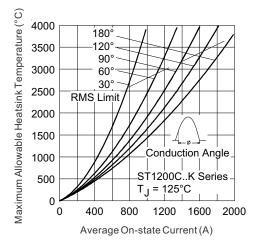


Fig. 5 - On-State Power Loss Characteristics

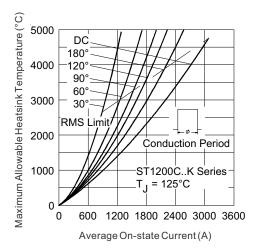


Fig. 6 - On-State Power Loss Characteristics

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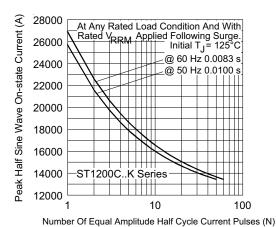


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

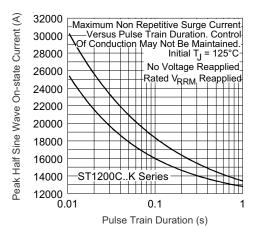


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

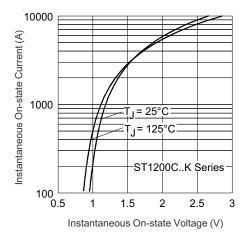


Fig. 9 - On-State Voltage Drop Characteristics

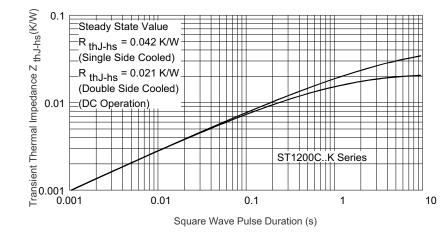


Fig. 10 - Thermal Impedance  $Z_{\text{thJ-hs}}$  Characteristics

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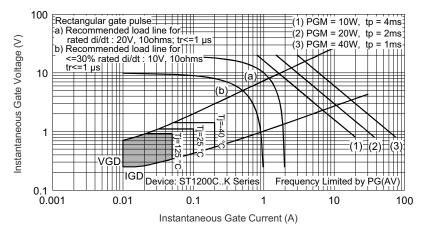
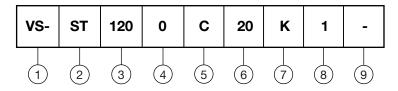


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

#### Device code



- Vishay Semiconductors product
- 2 Thyristor
- Essential part number
- 4 0 = converter grade
- 5 C = ceramic PUK
- 6 Voltage code: code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)
- 7 K = PUK case K-PUK (A-24)
- 8 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)
  - 1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)
- 9 Critical dV/dt: None = 500 V/µs (standard selection)
  - L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

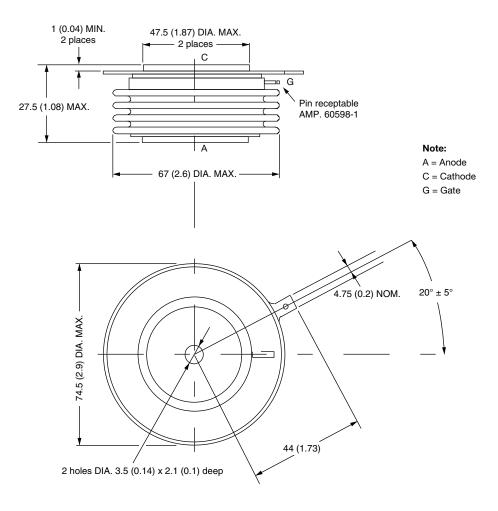


## Vishay Semiconductors

# K-PUK (A-24)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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